

<b>SANYO</b>	No.5363A	<b>2SC5302</b>
		NPN Triple Diffused Planar Silicon Transistor <b>Ultrahigh-Definition Color Display Horizontal Deflection Output Applications</b>

**Features**

- High speed ( $t_f = 100\text{ns typ.}$ )
- High breakdown voltage ( $V_{CBO} = 1500\text{V}$ ).
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.

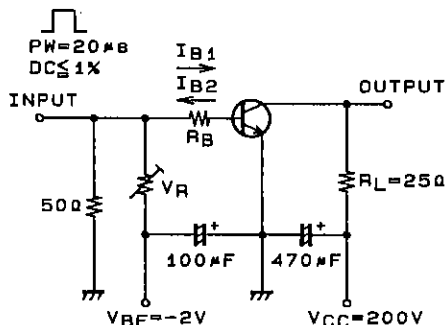
**Absolute Maximum Ratings at  $T_a = 25^\circ\text{C}$**

			unit
Collector-to-Base Voltage	$V_{CBO}$	1500	V
Collector-to-Emitter Voltage	$V_{CEO}$	800	V
Emitter-to-Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	15	A
Collector Current (Pulse)	$I_{CP}$	35	A
Collector Dissipation	$P_C$	3	W
	$T_c = 25^\circ\text{C}$	75	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics at  $T_a = 25^\circ\text{C}$**

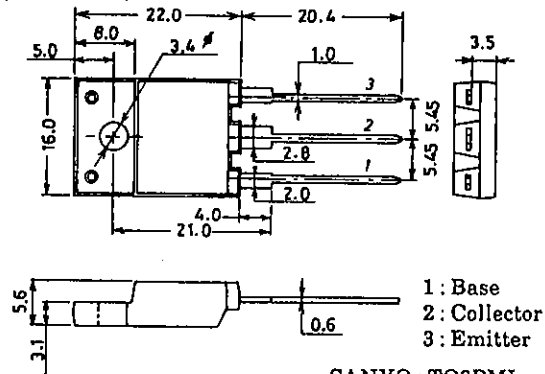
		min	typ	max	unit
Collector Cutoff Current	$I_{CES}$ $V_{CE} = 1500\text{V}, R_{BE} = 0$			1.0	mA
Collector Sustain Voltage	$V_{CEO(sus)}$ $I_C = 100\text{mA}, I_B = 0$	800			V
Emitter Cutoff Current	$I_{EBO}$ $V_{EB} = 4\text{V}, I_C = 0$			1.0	mA
Collector Cutoff Current	$I_{CBO}$ $V_{CB} = 800\text{V}, I_E = 0$			10	$\mu\text{A}$
DC Current Gain	$h_{FE(1)}$ $V_{CE} = 5\text{V}, I_C = 1.0\text{A}$	20		30	
	$h_{FE(2)}$ $V_{CE} = 5\text{V}, I_C = 12\text{A}$	4		7	
C-E Saturation Voltage	$V_{CE(sat)}$ $I_C = 12\text{A}, I_B = 3\text{A}$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$ $I_C = 12\text{A}, I_B = 3\text{A}$			1.5	V
Storage Time	$t_{stg}$ $I_C = 8\text{A}, I_{B1} = 1.6\text{A}, I_{B2} = -3.2\text{A}$			3.0	$\mu\text{s}$
Fall Time	$t_f$ $I_C = 8\text{A}, I_{B1} = 1.6\text{A}, I_{B2} = -3.2\text{A}$			0.2	$\mu\text{s}$

**Switching Time Test Circuit**



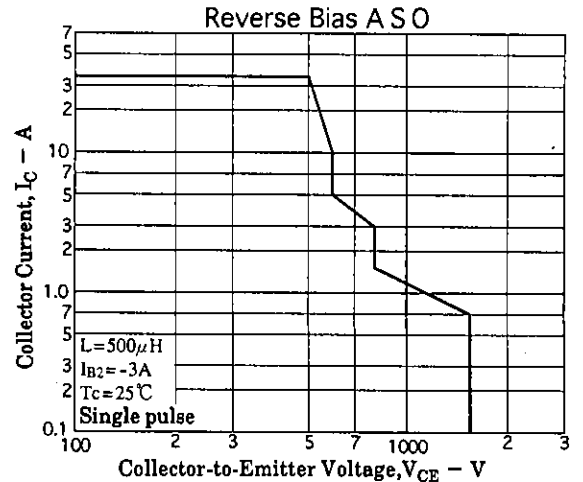
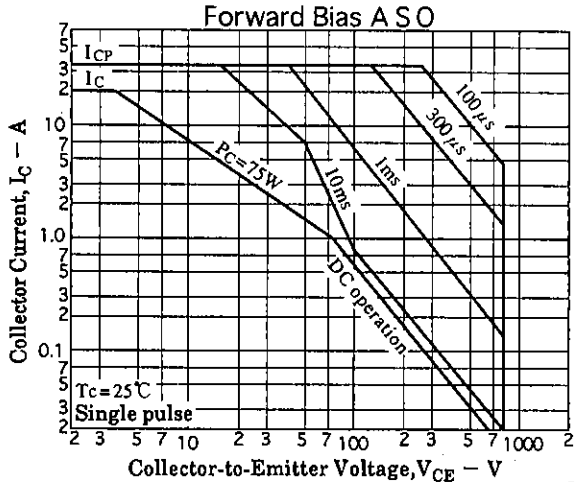
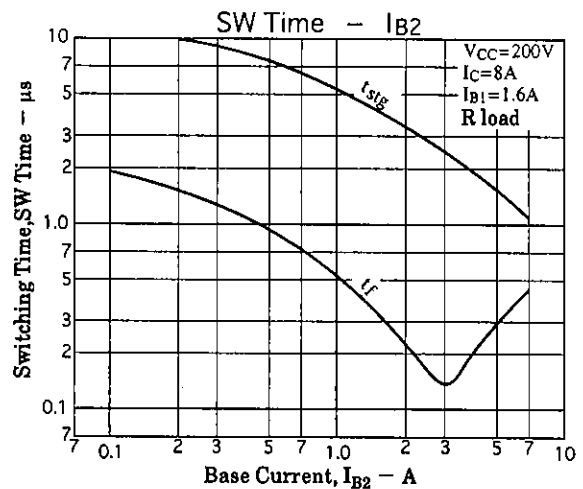
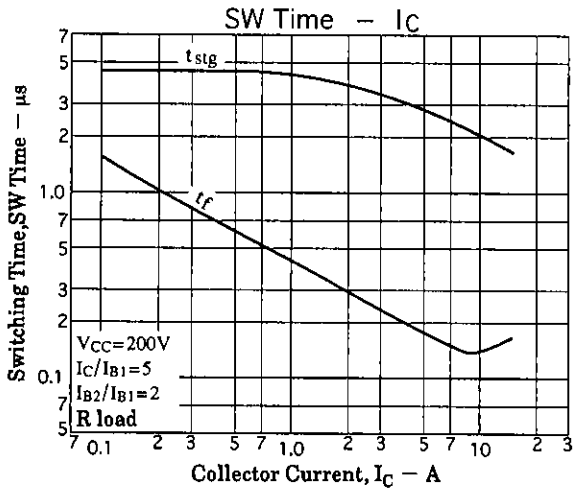
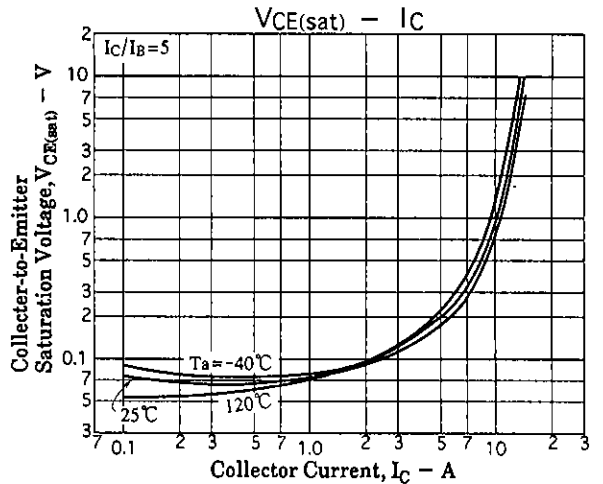
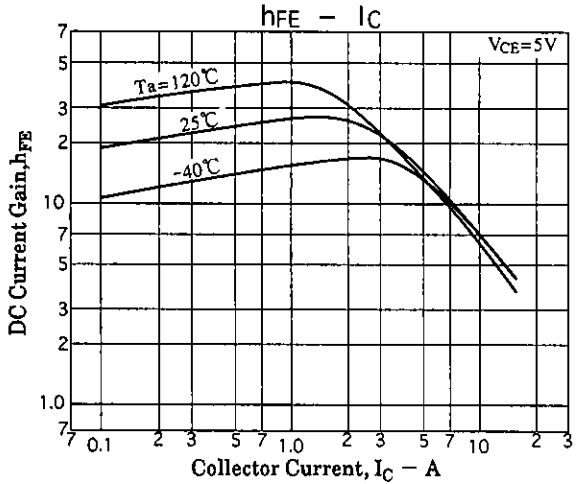
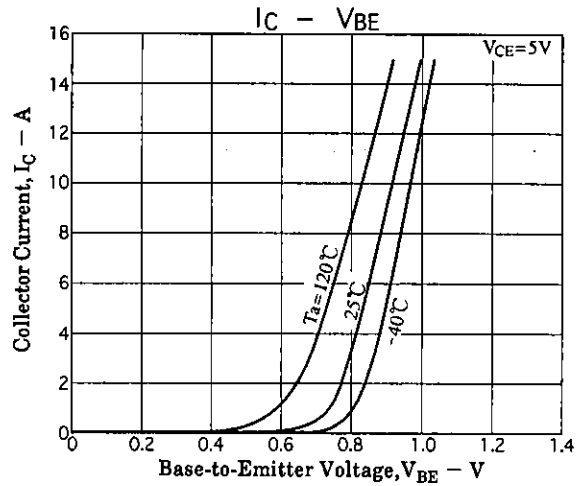
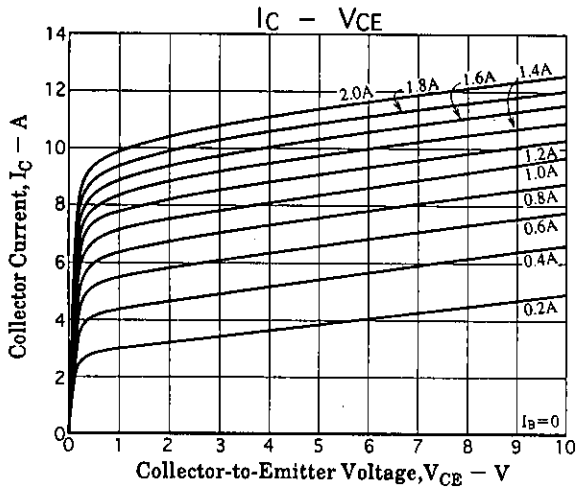
**Package Dimensions 2039C**

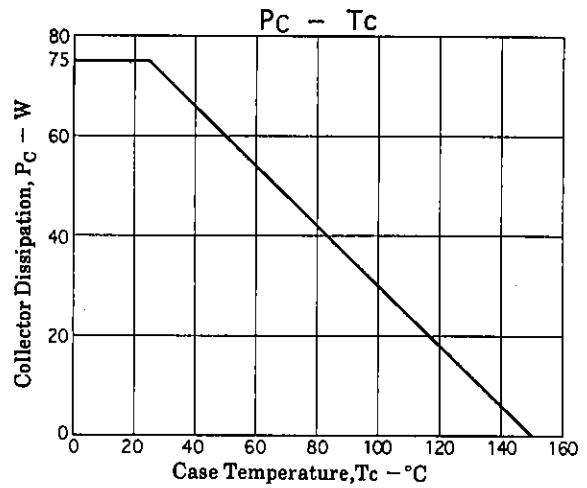
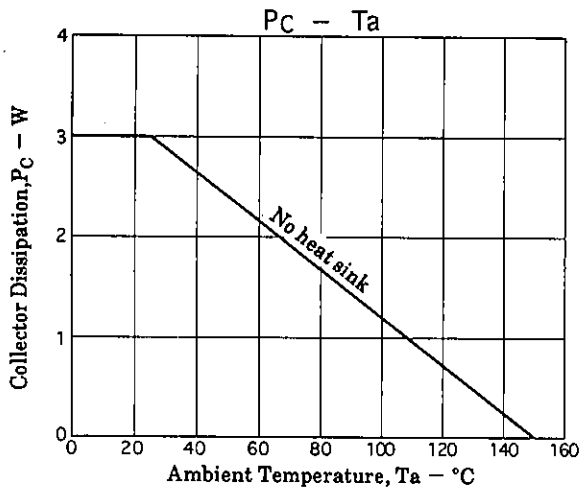
(unit : mm)



SANYO: TO3PML

**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**  
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN





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